GB02SLT12-214

Silicon Carbide Power Schottky Diode

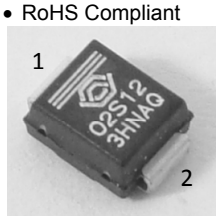
V_{RRM}	=	1200 V
$I_{F\ (Tc = 25°C)}$	=	5 A
$I_{F\ (Tc \leq 150°C)}$	=	2 A
Q_C	=	9 nC

Features

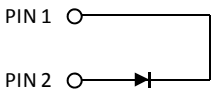
- Industry's leading low leakage currents
- 175 °C maximum operating temperature
- Temperature independent switching behavior
- Superior surge current capability
- Positive temperature coefficient of V_F
- Extremely fast switching speeds
- Superior figure of merit Q_C/I_F

Package

- RoHS Compliant



SMB / DO – 214AA



Advantages

- Low standby power losses
- Improved circuit efficiency (Lower overall cost)
- Low switching losses
- Ease of paralleling devices without thermal runaway
- Smaller heat sink requirements
- Low reverse recovery current
- Low device capacitance
- Low reverse leakage current at operating temperature

Applications

- Power Factor Correction (PFC)
- Switched-Mode Power Supply (SMPS)
- Solar Inverters
- Wind Turbine Inverters
- Motor Drives
- Induction Heating
- Uninterruptible Power Supply (UPS)
- High Voltage Multipliers

Maximum Ratings at T_j = 175 °C, unless otherwise specified

Parameter	Symbol	Conditions	Values	Unit
Repetitive peak reverse voltage	V_{RRM}		1200	V
Continuous forward current	I_F	T_C = 25 °C	5	A
Continuous forward current	I_F	T_C ≤ 150 °C	2	A
RMS forward current	$I_{F(RMS)}$	T_C ≤ 150 °C	3	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	T_C = 25 °C, t_P = 10 ms T_C = 150 °C, t_P = 10 ms	18 15	A
Non-repetitive peak forward current	$I_{F,max}$	T_C = 25 °C, t_P = 10 µs	100	A
I^2t value	$\int i^2\,dt$	T_C = 25 °C, t_P = 10 ms T_C = 150 °C, t_P = 10 ms	1.6 1.1	A^2s
Power dissipation	P_{tot}	T_C = 25 °C	65	W
Operating and storage temperature	T_j , T_{stg}		-55 to 175	°C

Electrical Characteristics at T_j = 175 °C, unless otherwise specified

Parameter	Symbol	Conditions		Values min.	Values typ.	Values max.	Unit
Diode forward voltage	V_F	I_F = 2 A, T_j = 25 °C I_F = 2 A, T_j = 175 °C			1.5 2.6	1.8 3.0	V
Reverse current	I_R	V_R = 1200 V, T_j = 25 °C V_R = 1200 V, T_j = 175 °C			5 10	50 100	µA
Total capacitive charge	Q_C	$I_F \leq I_{F,MAX}$ dI_F/dt = 200 A/µs T_j = 175 °C	V_R = 400 V V_R = 960 V		9 14		nC
Switching time	t_s		V_R = 400 V V_R = 960 V		< 17		ns
Total capacitance	C	V_R = 1 V, f = 1 MHz, T_j = 25 °C V_R = 400 V, f = 1 MHz, T_j = 25 °C V_R = 1000 V, f = 1 MHz, T_j = 25 °C			131 12 8		pF

Thermal Characteristics

Thermal resistance, junction - case	R_{thJC}	2.3	°C/W

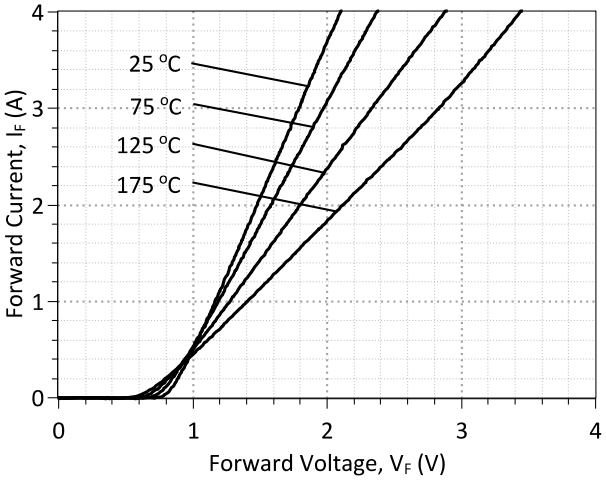


Figure 1: Typical Forward Characteristics

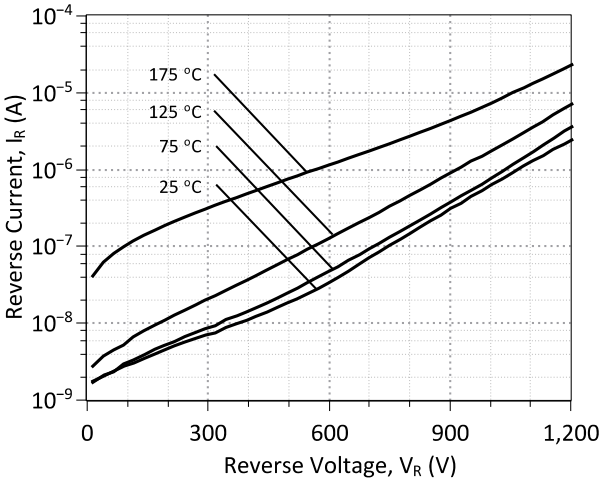


Figure 2: Typical Reverse Characteristics

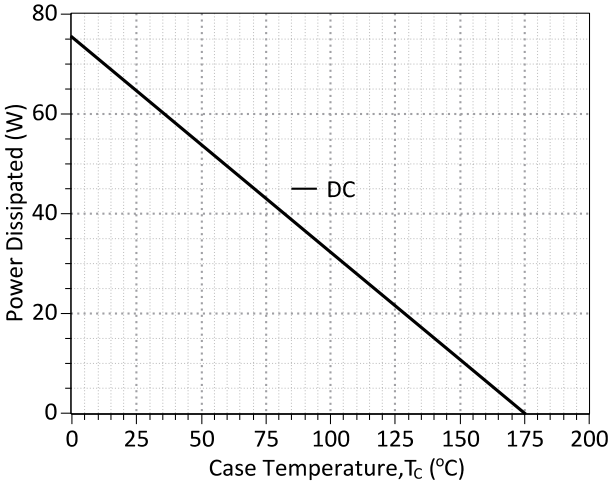


Figure 3: Power Derating Curve

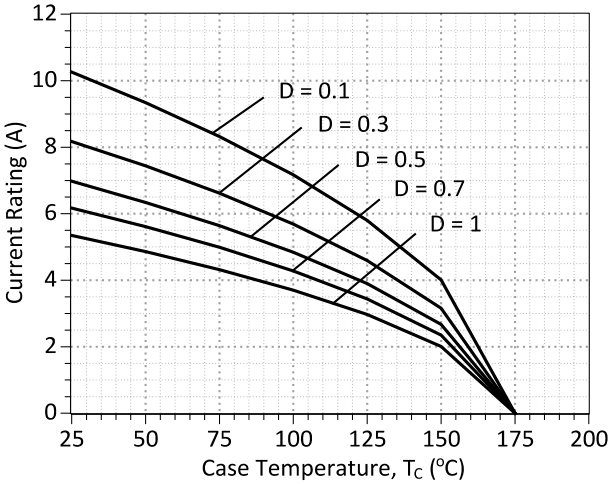


Figure 4: Current Derating Curves (D = t_P/T, t_P= 400 µs) (Considering worst case Z_{th} conditions)

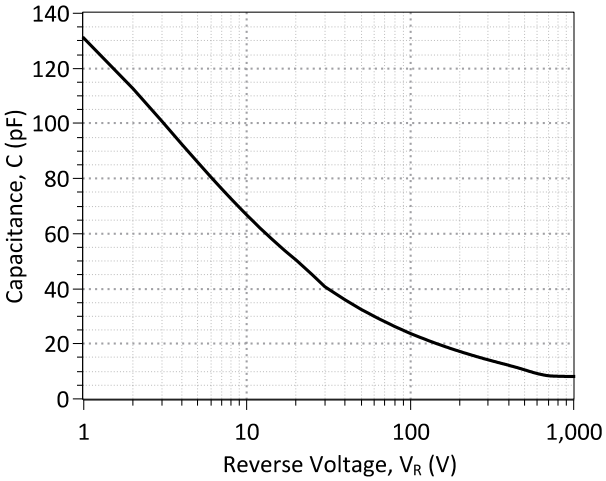


Figure 5: Typical Junction Capacitance vs Reverse Voltage Characteristics

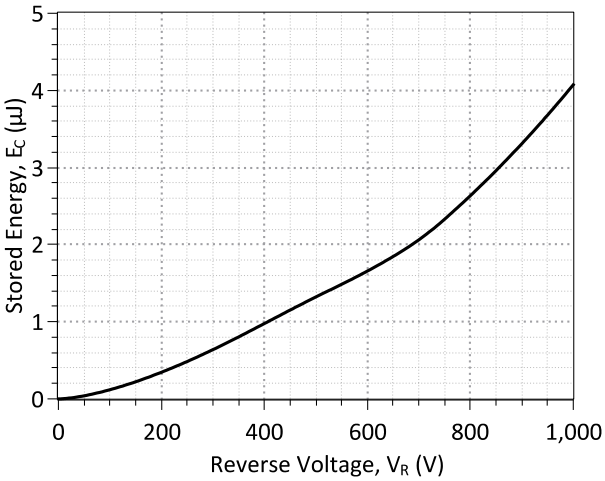


Figure 6: Typical Capacitive Energy vs Reverse Voltage Characteristics

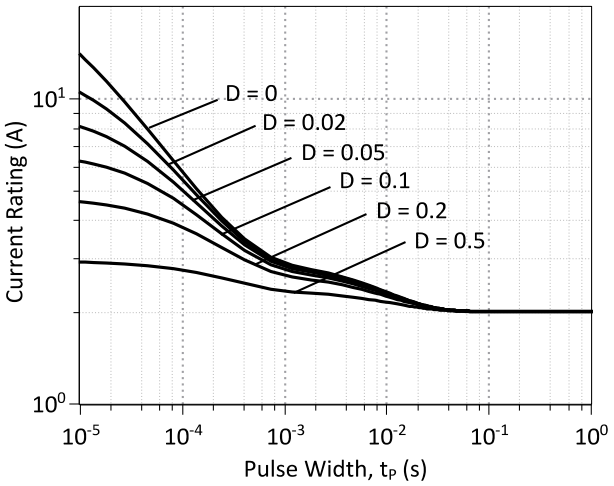


Figure 7: Current vs Pulse Duration Curves at T_C = 160 °C

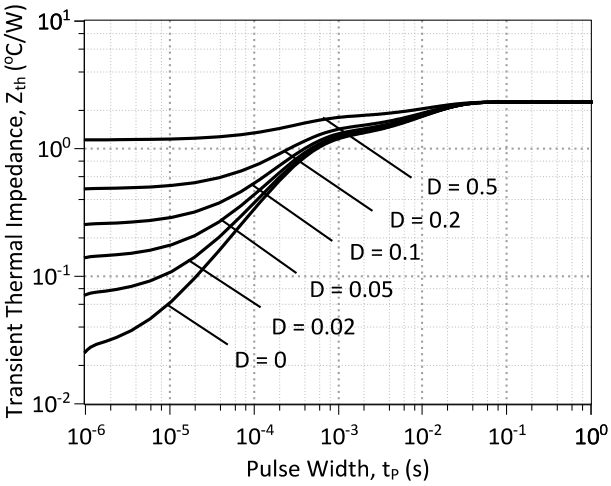
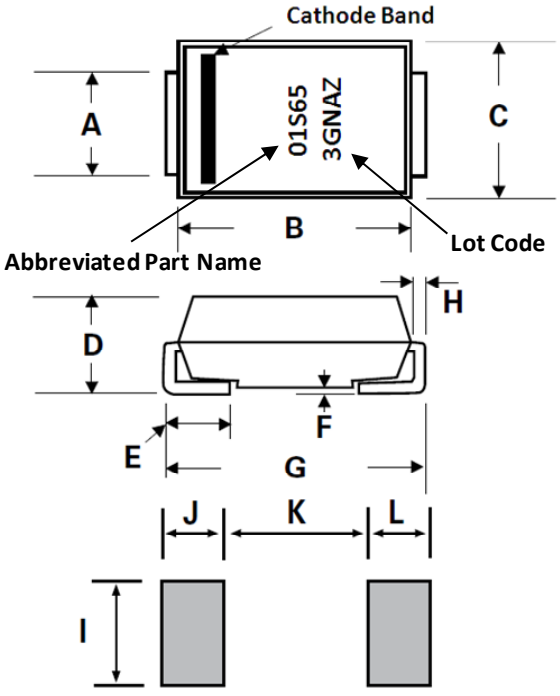


Figure 8: Transient Thermal Impedance

Package Dimensions:

SMB / DO - 214AA **PACKAGE OUTLINE**



Dimensions	Inches		Millimeters	
	Min	Max	Min	Max
A	0.077	0.086	1.950	2.200
B	0.160	0.180	4.060	4.570
C	0.130	0.155	3.300	3.940
D	0.084	0.096	2.130	2.440
E	0.030	0.060	0.760	1.520
F	-	0.008	-	0.203
G	0.205	0.220	5.210	5.590
H	0.006	0.012	0.152	0.305
I	0.089	-	2.260	-
J	0.085	-	2.160	-
K	-	0.107	-	2.740
L	0.085	-	2.160	-

NOTE
1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS

Revision History			
Date	Revision	Comments	Supersedes
2014/08/26	1	Updated Electrical Characteristics	
2013/09/09	0	Initial release	

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SPICE Model Parameters

This is a secure document. Please copy this code from the SPICE model PDF file on our website (http://www.genesicsemi.com/images/products_sic/rectifiers/GB02SLT12-214_SPICE.pdf) into LTSPICE (version 4) software for simulation of the GB02SLT12-214.

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*     MODEL OF GeneSiC Semiconductor Inc.
*
*     $Revision:   1.0           $
*     $Date:   09-SEP-2013       $
*
*     GeneSiC Semiconductor Inc.
*     43670 Trade Center Place Ste. 155
*     Dulles, VA 20166
*
*     COPYRIGHT (C) 2013 GeneSiC Semiconductor Inc.
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*
* These models are provided "AS IS, WHERE IS, AND WITH NO WARRANTY
* OF ANY KIND EITHER EXPRESSED OR IMPLIED, INCLUDING BUT NOT LIMITED
* TO ANY IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A
* PARTICULAR PURPOSE."
* Models accurate up to 2 times rated drain current.
*
* Start of GB02SLT12-214 SPICE Model
*
.SUBCKT GB02SLT12 ANODE KATHODE
D1 ANODE KATHODE GB02SLT12
D2 ANODE KATHODE GB02SLT12_PIN
.MODEL GB02SLT12 D
+ IS       2.05E-15        RS         0.282
+ TRS1     0.0054          TRS2       3E-05
+ N        1               IKF        251
+ EG       1.2             XTI        -1.8
+ CJO      1.61E-10        VJ         0.4508
+ M        1.586           FC         0.5
+ TT       1.00E-10        BV         1200
+ IBV      1.00E-03        VPK        1200
+ IAVE     2               TYPE       SiC_Schottky
+ MFG      GeneSiC_Semi
.MODEL GB02SLT12_PIN D
+ IS       1.54E-25        RS         0.39
+ TRS1     -0.003          N          3.941
+ EG       3.23            IKF        19
+ XTI      0               FC         0.5
+ TT       0               BV         1200
+ IBV      1.00E-03        VPK        1200
+ IAVE     10              TYPE       SiC_PiN
.ENDS
*
* End of GB02SLT12-214 SPICE Model
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